FGW40N120W

http://www.fujielectric.com/products/semiconductor/ Discrete IGBT

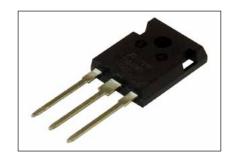
Discrete IGBT (High-Speed W series) 1200V / 40A

■ Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

Applications

Uninterruptible power supply PV Power coditionner Inverter welding machine



■ Equivalent circuit

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter Voltage	Vces	1200	V	
Gate-Emitter Voltage	V _{GES}	±20	V	
DC Collector Current	Ic@25	65	Α	Tc=25°C, Tj=150°C
	Ic@100	40	Α	Tc=100°C, Tj=150°C
Pulsed Collector Current	Icp	160	Α	Note *1
Turn-Off Safe Operating Area	-	160	Α	Vce≤1200V, Tj≤175°C
Short Circuit Withstand Time	t _{sc} 5	5	110	Vcc≤600V, VgE=15V
	tsc	5 µs	T _i ≤150°C	
IGBT Max. Power Dissipation	P□	430	W	Tc=25°C
Operating Junction Temperature	T _j	-40 ~ +175	°C	
Storage Temperature	T _{stg}	-55 ~ +175	°C	

Gate

Note *1 : Pulse width limited by Tjmax.

● Electrical characteristics (at T_j= 25°C unless otherwise specified)

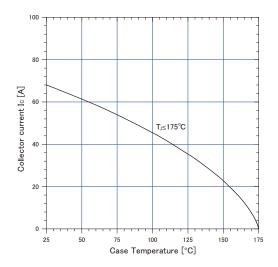
Description	Cumbala	Conditions		Characteristics			Units
Description	Symbols			min.	typ.	max.	Units
Zava Cata Valtaga Callagtay Current		\/ = 1200\/ \/ = 0\/	T _j =25°C	-	-	250	μA
Zero Gate Voltage Collector Current	ICES	$V_{CE} = 1200V, V_{GE} = 0V$	T _j =175°C	-	-	2	mA
Gate-Emitter Leakage Current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	200	nA
Gate-Emitter Threshold Voltage	V _{GE (th)}	V _{CE} = +20V, I _C = 40mA		5.0	6.0	7.0	V
Collector-Emitter Saturation Voltage	V _{CE} (sat)	V _{GE} = +15V, I _C = 40A	T _i =25°C T _i =175°C	-	2.0	2.6	V
Input Capacitance	Cies	Vc=25V	11) 1700	-	2500	-	
Output Capacitance	Coes	V _{GE} =0V		-	110	-	pF
Reverse Transfer Capacitance	Cres	f=1MHz		-	34	-	
Gate Charge	Q _G	V _{cc} = 400V I _c = 40A V _{GE} = 15V		-	120	-	nC
Turn-On Delay Time	t _{d(on)}	T _i = 25°C - V _{cc} = 600V - I _c = 40A -		-	32	-	ns
Rise Time	t			-	54	-	
Turn-Off Delay Time	t _{d(off)}			-	178	-	
Fall Time	tr	V _{GE} = 15V		-	40	-	
Turn-On Energy	Eon	$R_G = 10\Omega$		-	2.8	-	
Turn-Off Energy	Eoff	L = 500µH Energy loss include "tail" and FWD (FDRW20S120J) reverse recovery.		-	1.6	-	mJ
Turn-On Delay Time	t _{d(on)}	T _i = 150°C		-	32	-	
Rise Time	t	V _{cc} = 600V - 48 I _c = 40A - 220		-	48	-	ns
Turn-Off Delay Time	t _{d(off)}			220	-	115	
Fall Time	tr	V _{GE} = 15V		-	56	-	
Turn-On Energy	Eon	$R_G = 10\Omega$		-	4.6	-	
Turn-Off Energy	Eoff	L = 500µH Energy loss include "tail" a (FDRW20S120J) reverse		-	2.4	-	mJ

Thermal resistance characteristics

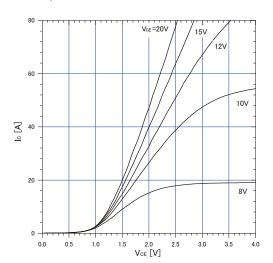
Items	Symbols Conditions	Characteristics			Units	
		min.	typ.	max.	Units	
Thermal Resistance, Junction-Ambient	R _{th(j-a)}	-	-	-	50	°C/W
Thermal Resistance, Junction to Case	R _{th(j-c)_IGBT}	-	-	-	0.347	C/VV

■ Characteristics (Representative)

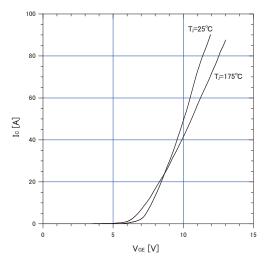
Graph.1 DC Collector Current vs T_c $V_{ce} \ge +15V$, $T_i \le 175$ °C



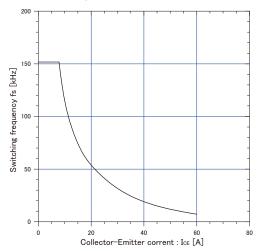
Graph.3 Typical Output Characteristics (V_{ce} - I_c) T_r =25°C



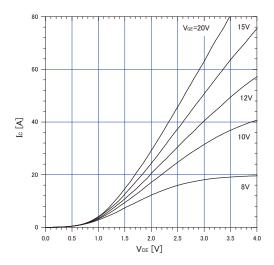
Graph.5
Typical Transfer Characteristics
V_{s∈}=+15V



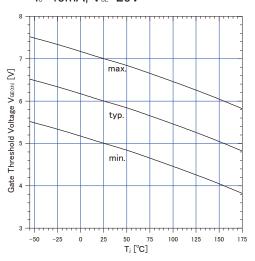
Graph.2 Collector Current vs. switching frequency V_{GE} =+15V, T_{C} ≤175°C, V_{CC} =600V, D=0.5, R_{G} =10 Ω , T_{C} =100°C



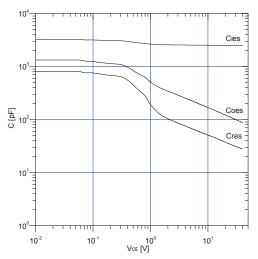
Graph.4
Typical Output Characteristics (VcE-Ic)
T_i=175°C



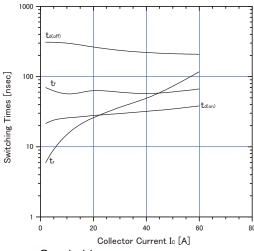
Graph.6
Gate Threshold Voltage vs. T₁
I₀=40mA, V₀₀=20V



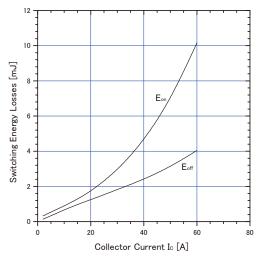
Graph.7 Typical Capacitance V_e=0V,f=1MHz,T_i=25°C



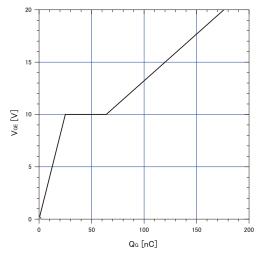
Graph.9
Typical switching time vs. I_c $T_r=175^{\circ}C_rV_{cc}=600V_rL=500\mu H$ $V_{cc}=15V_rR_c=10\Omega$



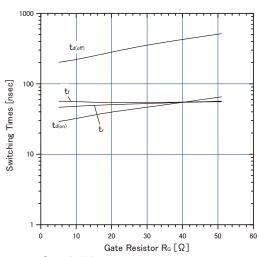
Graph.11 Typical switching losses vs. Io T_i=175°C,V_{co}=600V,L=500 μ H V_{oe}=15V,R_o=10 Ω



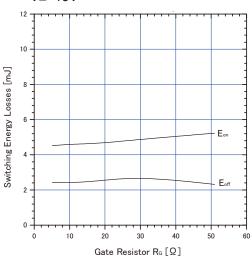
Graph.8 Typical Gate Charge Vcc=600V,Ic=40A,T,=25°C



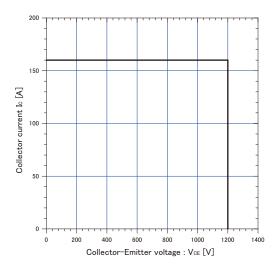
Graph.10
Typical switching time vs. R_s
T_i=175°C,V_{cc}=600V,I_c=40A,L=500μH
V_{se}=15V



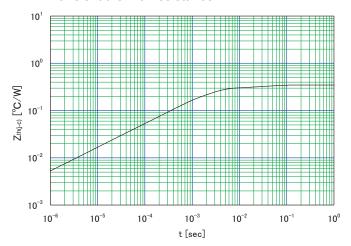
Graph.12
Typical switching losses vs. R_o
T_i=175°C,V_{oc}=600V,I_o=40A,L=500μH
V_{oe}=15V



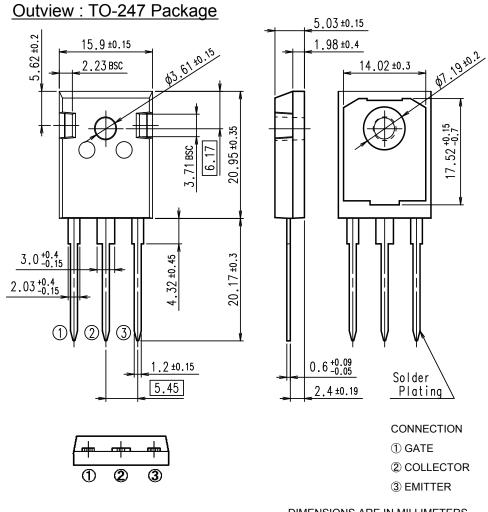
Graph.13 Reverse biased Safe Operating Area $T_i \le 175^{\circ}C, V_{\text{GE}} = +15 \text{V}/0\text{V}, R_{\text{G}} = 10\Omega$



Graph.14
Transient thermal resistance



■ Outline Drawings, mm



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